



QUAD TVS/ZENER ARRAY FOR ESD AND LATCH-UP PROTECTION

This Quad TVS/Zener Array family have been designed to Protect Sensitive Equipment against ESD and to prevent Latch-Up events in CMOS circuity operating at 5V,12V,15V and 24V. This TVS array offers an integrated sloution to protect up to 4 data lines where the board space is

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FEATURES

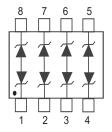
- 350W Power Dissipation (8/20µs Waveform)
- Low Leakage Current, Maximum of $5\mu A$ at rated voltage
- Very Low Clamping Voltage
- IEC61000-4-2 ESD 20kV air,15kV Contact Compliance
- In compliance with EU RoHS 2002/95/EC directives

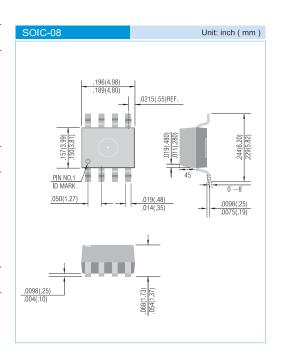
MECHANICAL DATA

- Case: SOIC-08, Molded plastic over passivated junction
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.079 grams
- Mounting Position : Any

APPLICATIONS

- RS-232C or RS-422 Communication ports
- GPIB/IEEE 485 Ports
- Portable Instrumentation





MAXIMUM RATINGS (Per Device)

Rating	Symbol	Value	Units
Peak Pulse Power (8/20μs Waveform)	P _{PP}	350	W
ESD Voltage (HBM) Per MIL-STD-883C	V _{ESD}	>25	kV
Operating Temperature Range	T _J	-50 to +150	°C
Storage Temperature Range	T _{stg}	-50 to +150	°C





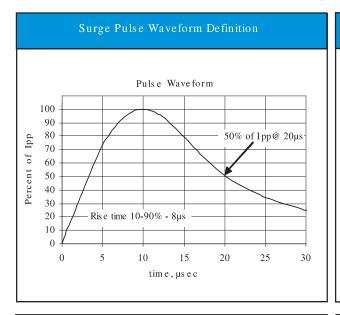
ELECTRICAL CHARACTERISTICS (PER DEVICE) TJ = 25°C

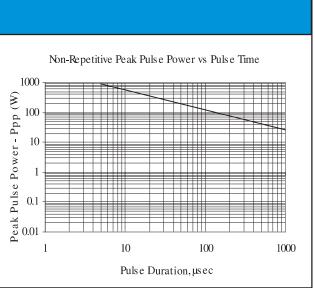
Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
	-	Condition	141111.	тур.		V
Reverse Stand-Off Voltage	VRWM		-	-	5	
Reverse Breakdown Voltage	VBR	I BR=1mA	6	-	-	V
Reverse Leakage Current	IR	V _R =5V	-	-	5	μА
Clamping Voltage (8/20µs)	Vc	IPP=5A	-	-	9.8	V
Clamping Voltage (8/20µs)	Vc	IPP=24A	-	-	13	V
Off State Junction Capacitance	CJ	0 Vdc Bias f=1MHz	-	270	300	pF
Off State Junction Capacitance	Сл	5 Vdc Bias f=1MHz	-	200	230	pF
PJSMDA12C Marking DC2						
Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	VRWM		-	-	12	V
Reverse Breakdown Voltage	VBR	I BR=1mA	13.3	-	-	V
Reverse Leakage Current	IR	V _R =5V	-	-	5	μΑ
Clamping Voltage (8/20μs)	Vc	IPP=5A	-	-	20	V
Clamping Voltage (8/20μs)	Vc	I PP=15A	-	-	25	V
Off State Junction Capacitance	Сл	0 Vdc Bias f=1MHz	-	-	150	pF
PJSMDA15C Marking DCC				I.		
Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	VRWM		-	-	15	V
Reverse Breakdown Voltage	VBR	I BR=1mA	16.7	-	-	V
Reverse Leakage Current	IR	V _R =5V	-	-	5	μА
Clamping Voltage (8/20µs)	Vc	IPP=5A	-	-	24	V
Clamping Voltage (8/20µs)	Vc	I PP=12A	-	-	29	V
Off State Junction Capacitance	CJ	0 Vdc Bias f=1MHz	_	-	100	pF
PJSMDA24C Marking DC4						
Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	VRWM		_	-	24	V
Reverse Breakdown Voltage	VBR	IBR=1mA	26.7	-	-	V
Reverse Leakage Current	IR	V _R =5V	-	_	5	μА
Clamping Voltage (8/20µs)	Vc	IPP=5A	_	_	40	V
Clamping Voltage (8/20μs)	Vc	IPP=8A			44	
	VC	0 Vdc Bias f=1MHz	-	-	60	pF

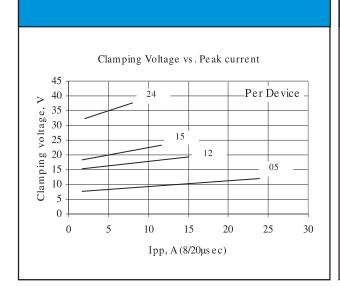


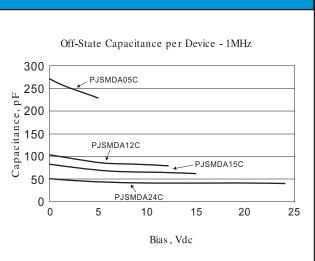


TYPICAL CHARACTERISTICS T_J = 25°C unless otherwise noted





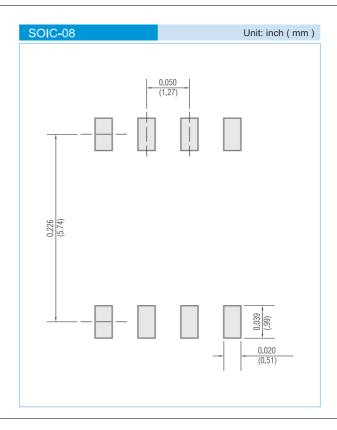








MOUNTING PAD LAYOUT



ORDER INFORMATION

· Packing information

T/R - 3K per 13" plastic Reel

LEGAL STATEMENT

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